



SE03N6S01GZ ESD Array Low Capacitance ESD Protection Operating Voltage 3.3V IR Maximum 0.5μA

Our Product Introduction

Basic Information

- Place of Origin: Shenzhen Guangdong China
- Brand Name: SOCAY
- Certification: REACH RoHS ISO
- Model Number: SE03N6S01GZ
- Minimum Order Quantity: 10000PCS
- Price: Negotiable
- Delivery Time: 5-8 work days



Product Specification

- Component Name: ESD Arrays
- Component Package: DFN1006-2L
- Vrwm (Max.): 3.3V
- Vbr (Min.): 5.0V
- Vbr (Max.): 5.0V
- It: 1mA
- Ir (Max.): 0.5μA
- Vc (Typ.) (Ipp=1A): 6.0V
- Vc (Typ.) (Ipp=5A): 10.0V
- Cgd: 12pF
- Highlight: SE03N6S01GZ ESD Array, 3.3V ESD Array, Low Capacitance ESD Array

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Product Description

Low Capacitance ESD Arrays for ESD Protection SE03N6L01GZ Operating Voltage 3.3V

ESD Arrays Features:

Operating Voltage: 3.3V
 Low Leakage: nA Level
 Low Capacitance
 Extremely-Low Clamping Voltage
 RoHS compliant

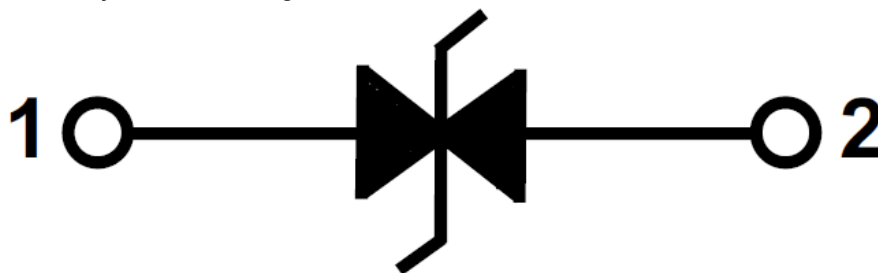
ESD Arrays Applications:

Cellular Handsets & Accessories
 Digital Visual Interface (DVI)
 RF Circuits
 Display Port
 USB Ports
 MDDI Ports
 PCI Express

ESD Arrays Mechanical Characteristics:

DFN1006 (1.0x0.6x0.5mm) Package
 Weight 0.5 Milligrams (Approximate)
 Quantity Per Reel : 10,000pcs
 Reel Size : 7 inch
 Lead Finish : Lead Free

ESD Arrays Functional Diagram:



ESD Arrays Absolute Maximum Ratings ($T_A=25$ unless otherwise specified):

Symbol	Parameter	Value	Units
T_L	Lead Soldering Temperature	260 (10sec)	$^{\circ}\text{C}$
T_{OP}	Operating Temperature Range	-55 to +125	
T_{STG}	Storage Temperature Range	-55 to +150	
V_{ESD}	ESD per IEC61000-4-2 (Air)	± 25	kV
	ESD per IEC61000-4-2 (Contact)	± 25	

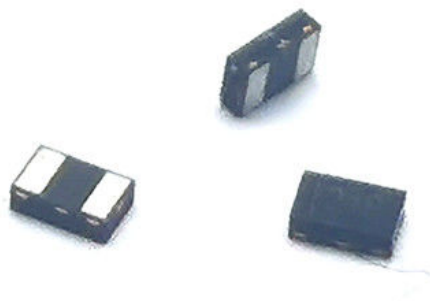
Electrical Characteristics ($T_A = 25$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Working Voltage	VRWM	--	--	--	3.3	V
Breakdown Voltage	VBR	IT = 1mA	3.5	5.1	5.0	V
Leakage Current	IR	VRWM = 3.3V	--	--	0.5	μA
Clamping Voltage	VC	IPP = 1A, tP = 8/20 μs	--	6.0	--	V
Clamping Voltage	VC	IPP = 5A, tP = 8/20 μs	--	10.0	--	V
Junction Capacitance	CJ	VR = 0V, f = 1MHz	--	0.5	--	pF

DFN1006-2L Package Outline & Dimensions:

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.070	0.000	0.003
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.450 REF		0.018 REF	
E1	0.400 REF		0.016 REF	
b	0.275	0.325	0.011	0.013
e	0.675	0.725	0.027	0.029

L	0.275	0.325	0.011	0.013
L1	0.010 REF		0.000 REF	



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